

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

On page 1, after the title, please insert the following:

--This application is a continuation of Application Serial No. 09/840,291 filed April 24^V, 2001, *DR(3/9/04)*
now U.S. Patent 6,623,895, which is a CIP of 09/562,443 filed *DR(3/9/04)*
2001-05/01/2000 now ABANDONED, *DR(3/9/04)*

HYBRID PHASE-SHIFT MASK

~~This application is a continuation-in-part of application Serial No. 09/562,443, which was filed on May 1, 2000.~~

3/19/04

Field Of The Invention

The present invention relates to the design of photomasks ("masks") for use in lithography, and more particularly, to the use of a hybrid mask which provides for the formation of both phase-shifted and non-phase-shifted features with a single exposure.

The present invention also relates to the use of such a mask in a lithographic apparatus, comprising for example:

- a radiation system for supplying a projection beam of radiation;
- a mask table for holding the mask;
- 10 - a substrate table for holding a substrate; and
- a projection system for projecting at least part of a pattern on the mask onto a target portion of the substrate.

Background Of The Invention

Lithographic apparatus can be used, for example, in the manufacture of integrated circuits (ICs). In such a case, the mask may contain a circuit pattern corresponding to an individual layer of the IC, and this pattern can be imaged onto a target portion (e.g. comprising one or more dies) on a substrate (silicon wafer) that has been coated with a layer of radiation-sensitive material (resist). In general, a single wafer will contain a whole network of adjacent target portions that are successively irradiated via the projection system, one at a time. In one type of lithographic projection apparatus, each target portion is irradiated by exposing the entire mask pattern onto the target portion in one go; such an apparatus is commonly referred to as a wafer stepper. In an alternative apparatus — commonly referred to as a step-and-scan apparatus — each target portion is irradiated by progressively scanning the mask pattern under the projection beam in a given reference direction (the "scanning" direction) while synchronously scanning the substrate table parallel or anti-parallel to this direction; since, in general, the projection system will have a magnification factor M (generally < 1), the speed V at which the substrate table is scanned will be a factor M times that at which the mask table is scanned. More